

40CPQ080 40CPQ100

Technical Data Data Sheet N0697, Rev. A

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40CPQ080/40CPQ100 SCHOTTKY RECTIFIER



Circuit Diagram

Common Cathode 2 4 4 4 Anode Anode

Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	80(40CPQ080) 100(40CPQ100)	V	
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=145°C, rectangular wave form	20(Per Leg) 40(Per Device)	A	
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse, T _C = 25 °C	360	А	
Non-Repetitive Avalanche Energy(Per Leg)	E _{AS}	TJ=25℃, I _{AS} =2A, L=90. mH	11.25	mJ	
Repetitive Avalanche Current(Per Leg)	I _{AR}	Current decaying linearly to zero in 1 μ sec Frequency limited by T _J max. V _A =1.5×V _R typical	0.75	A	

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop (Per Leg)*	V_{F1}	@ 20A, Pulse, TJ = 25 °C @ 40A, Pulse, TJ = 25 °C	0.74 0.80	0.79 0.91	V
	Vf2	@ 20A, Pulse, TJ = 125 °C @ 40A, Pulse, TJ = 125 °C	0.56 0.65	0.61 0.75	V
Reverse Current	I _{R1}	$@V_R = rated V_{R_j}T_J = 25 \ ^{\circ}C$	0.0006	1.0	mA
(Per Leg)*	I _{R2}	$@V_R = rated V_{R_j}T_J = 125 \circ C$	0.4	15.0	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25 \circ C, f_{SIG} = 1MHz$	800	900	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/µs

 $^{*}\,$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%

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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units	
Junction Temperature	TJ	-	-55 to +150	°C	
Storage Temperature	T _{stg}	-	-55 to +150	°C	
Typical Thermal Resistance Junction to	R _{e.IC} DC operation		1.25(per leg)	°C/W	
Case	R _{θJC}		0.63(per device)	-0/00	
Typical Thermal Resistance, case to Heat Sink	$R_{ hetacs}$	Mounting surface, smooth and greased	0.24	°C/W	
Approximate Weight	wt	-	6.28	g	
Case Style	TO-247AD				

Ratings and Characteristics Curves



Typical Forward Characteristics

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Typical Reverse Characteristics

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Mechanical Dimensions TO-247AD

A1-





SYMPOL	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
А	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.40		
b1	1.80	2.00	2.20		
b2	2.80	3.00	3.20		
с	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.55			
D2		1.20			
E	15.45	15.80	16.00		
E1		13.30			
E2		5.00			
E3		2.50			
е		5.44			
L	19.42	19.92	20.70		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1		7.40		
P2		2.50			
Q		5.80			
S	6.05	6.15	6.25		
Т		10.00			
U		6.20			

Ordering Information:

Device	Package	Shipping	
40CPQ080(100)	TO-247AD(Pb-Free)	25pcs / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification



Marking Diagram



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